

**Description**

The SX80P10T uses advanced technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -100V$   $I_D = -80A$

$R_{DS(ON)} < 25m\Omega$  @  $V_{GS} = 10V$

$C_{iss} \approx 4230\text{ PF}$

**Application**

Brushless motor

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-80	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-56	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-300	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	174	mJ
$I_{AS}$	Avalanche Current	-50	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	280	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	0.65	°C/W

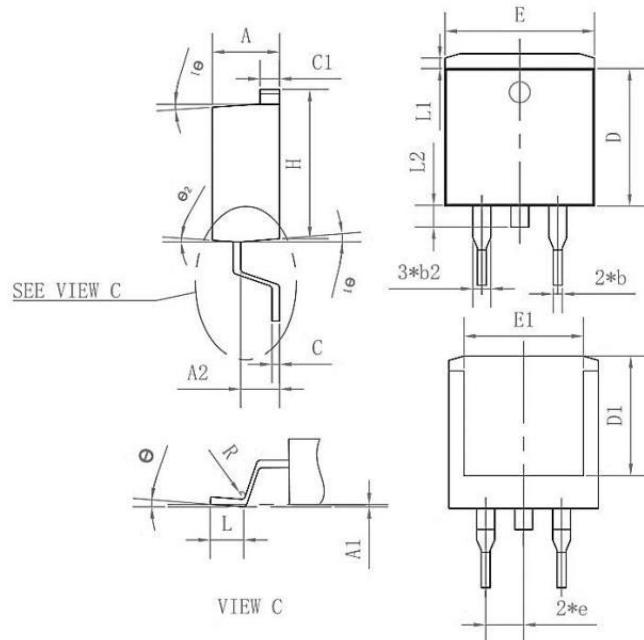
**P-Channel Electrical Characteristics (T<sub>J</sub> =25 °C, unless otherwise noted)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-100	-	-	V
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V,	-	-	-1.0	μA
IGSS	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.6	-2.5	V
RDS(on)	Static Drain-Source on-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	19	25	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	-	25	30	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V, f=1.0MHz	-	4230	-	pF
C <sub>oss</sub>	Output Capacitance		-	388	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	26	-	pF
Q <sub>g</sub>	Total Gate Charge		-	80	-	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-50V, I <sub>D</sub> =-5A, V <sub>GS</sub> =-10V	-	15.6	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	17.2	-	nC
td(on)	Turn-on Delay Time		-	26	-	ns
tr	Turn-on Rise Time	V <sub>DD</sub> =-50V, I <sub>D</sub> =-5A, R <sub>G</sub> =6Ω, V <sub>GS</sub> =-10V	-	78	-	ns
td(off)	Turn-off Delay Time		-	200	-	ns
tf	Turn-off Fall Time		-	210	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-80	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-	-280	A
VSD	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-30A	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	T <sub>J</sub> =25°C, I=-5A,dI/dt=100A/μs	-	208	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	560	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is VDD =-72V,VGS =-10V,L=0.1mH,IAS =-50A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

## Package Mechanical Data-TO-263-3L-SLK



Symbol	Common		
	Mim	mm Nom	Max
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.70
b	0.70	0.80	1.00
b2	1.25	1.36	1.50
C	0.45	0.50	0.55
C1	1.29	1.30	9.40
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
θ	0°	4°	8°
θ1	4°	7°	10°
θ2	0°	3°	6°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-263-3L		800